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Publication Date
2005-01-11

Peer reviewed
Perturbing the Superconducting Planes in CeCoIn$_5$ by Sn Substitution


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In contrast to substitution on the Co or Ce site, Sn substitution has a remarkably strong effect on superconductivity in CeCoIn$_{5-x}$Sn$_x$, with $T_c \to 0$ beyond only $\sim 3.6\%$ Sn. Instead of being randomly distributed on in-plane and out-of-plane In sites, extended x-ray absorption fine structure measurements show the Sn atoms preferentially substitute within the Ce-In plane. This result highlights the importance of the In(1) site to impurity scattering and clearly demonstrates the two-dimensional nature of superconductivity in CeCoIn$_5$.

PACS numbers: 72.15.Qm, 61.10.Ht, 71.23.-k, 71.27.-a

With the discovery of unconventional superconductivity (SC) in CeMIn$_5$ ($M =$ Co, Rh, or Ir), the study of the interplay between magnetism and SC has received much attention in the past few years. Various investigations have revealed that both SC and magnetic order coexist in CeCo$_{1-x}$Rh$_x$In$_5$ and CeIr$_{1-x}$Rh$_x$In$_5$ systems at ambient pressure over a wide range of concentrations [1–4]. There is also growing experimental evidence that these compounds are close to an antiferromagnetic quantum critical point in Doniach’s phase diagram, and that SC is mediated by magnetic fluctuations with an anisotropic superconducting gap, possibly even with $d$-wave symmetry [5–8]. Here, we address the nature of SC by directly perturbing the superconducting state in CeCoIn$_5$.

CeCoIn$_5$ is an ambient pressure superconductor that crystallizes in the HoCoGa$_5$-type tetragonal structure with a superconducting transition temperature $T_c = 2.3$ K [9]. In this structure (Fig. 1 inset) layers of CeIn$_3$-like planes and blocks of CoIn$_2$ are stacked sequentially along the $c$-axis giving rise to two inequivalent In sites: the In(1) site in the Ce plane and the In(2) site located between the Ce and Co planes. This system can therefore be thought of as a layered CeIn$_3$, a cubic antiferromagnet at ambient pressure and a superconductor at pressures above 2.6 GPa [10]. Compared to the cubic CeIn$_3$, however, $T_c$ is an order of magnitude greater in CeCoIn$_5$. This increase in $T_c$ has been attributed to the quasi-two dimensional (2D) structure [6, 9]. In fact, a local density approximation (LDA) calculation finds no relevant hybridization of cobalt $d$-orbitals with cerium $f$-band states, suggesting that the material can be thought of as a double-layered compound with two almost independent structures [11] as suggested by Shishido et al. [12]. Furthermore, average charge correlations between Ce and In(1) are higher than between Ce and In(2) in this calculation [11], implying a tendency toward electronic dynamics in two dimensions. Measurements of the de Haas-van Alphen effect also reveal a cylindrical Fermi surface, much more 2D-like than either CeIrIn$_5$ or CeRhIn$_5$, suggesting that the increasingly 2D electronic structure has a direct correlation with enhanced $T_c$ [13, 14].

In addition, solutions of Eliashberg equations suggest that in magnetically mediated superconductors quasi-2D structures are favored over 3D systems [15]. More evidence for the role of dimensionality in determining $T_c$ in the 115 compounds comes from crystallographic studies. A clear correlation between the $c/a$ ratio and $T_c$ has been observed in CeM$_{1-x}$N$_x$In$_5$ ($M =$ Ir, Rh, Co) and in the structurally related Pu-115 compounds [16–18]. Finally, critical field measurements in the (110) plane also suggests a 2D superconducting state in CeCoIn$_5$ [19].

Although this body of work provides strong circumstantial evidence for a 2D superconducting state, much of the evidence relates to the total Fermi surface, rather than to the superconducting piece. Some experimental work, however, aims at perturbing the superconducting state within the Ce-In planes, such as the $c/a$ ratio and the (110)-plane critical field studies. Site substitution offers the ability to perturb the superconducting state at particular sites in the unit cell. For instance, substitution onto the Co site has a relatively small effect on $T_c$, with SC persisting at least up to $75\%$ Rh in CeCo$_{1-x}$Rh$_x$In$_5$ [16]. This situation is in contrast to substituting La for Ce, where SC is observed only up to $15\%$ La substitution [20].

A recent study by Bauer et al. [21] shows that SC in the CeCoIn$_{5-x}$Sn$_x$ alloy is destroyed after only $\sim 3.6\%$ Sn for In, or $x = 0.18$ (Fig. 1). This suppression is not due to a difference in the $c/a$ ratio, since that ratio in CeCoIn$_{5-x}$Sn$_x$ is constant with $x$ [21]. This result clearly suggests that there is a direct perturbation of the superconducting state with the replacement of Sn
for In. The alloy CeCoIn$_{5-x}$Sn$_x$ is therefore an ideal system to explore the nature of SC in Ce-115 compounds. Moreover, it remains unclear why substituting on such a small percentage of In sites, only 20% of which are in the Ce plane, has such a large effect, especially compared to La substitution. In order to shed light on the mechanism by which SC is suppressed, we have carried out local structure investigations around the Sn atoms in CeCoIn$_{5-x}$Sn$_x$. X-ray absorption spectroscopy (XAS) is an excellent tool for studying both the local electronic and atomic structure of the atom being probed. The extended x-ray absorption fine structure (EXAFS), the region beyond ~10-20 eV in energy above the absorbing edge, contains information about the radial pair-distance functions around the absorbing species. We report Sn K-edge EXAFS measurements on CeCoIn$_{5-x}$Sn$_x$ ($x = 0.09, 0.12, 0.18,$ and 0.24) and discuss the results in relation to the observed bulk properties.

Details of sample growth and characterization are described elsewhere [9, 21, 22]. Single crystals of CeCoIn$_{5-x}$Sn$_x$ were grown in In flux in the ratio Ce:Co:In:Sn = 1:1:20:y ($y = 0.1, 0.2, 0.3,$ and 0.4). Microprobe analysis showed that the actual Sn concentration in the samples was $x \sim 0.6y$. Sn K-edge absorption spectra were measured in fluorescence mode using a Canberra 32-element germanium detector and a half-tuned double-crystal Si(220) monochromator at beamline 11-2 of the Stanford Synchrotron Radiation Laboratory (SSRL). The single crystal samples were ground with a mortar and pestle and passed through a 20 $\mu$m sieve. The powdered material was then brushed onto adhesive tape and several layers were stacked together. The samples were mounted in a liquid helium flow cryostat and data were recorded at 30 K.

The EXAFS data were analyzed using the RSXAP software package [23-25]. After pre-edge subtraction, the EXAFS function $\chi(k)$ was extracted from the measured absorption coefficient $\mu(k)$ according to $\chi(k) = \mu(k)/\mu_0(k) - 1$, where $\mu_0(k)$ is a smooth background function, the photoelectron wave vector $k = \hbar^{-1}[2m(E - E_0)]^{1/2}$, $m$ is the electron rest mass, $E$ is the incident energy and $E_0$ is the threshold energy. The smoothly varying background $\mu_0(k)$ was determined by fitting a 5-7 knot cubic spline function, through the data above the edge. The value for $E_0$ was determined arbitrarily from the half-height of the main edge. The Sn concentration was low enough that correcting the data for self-absorption effects was not necessary. Structural refinements of the EXAFS data were performed in $R$-space by fitting data to theoretical standards generated by FEFF7 [26]. Representative $k$-space data are shown in Fig. 2.

The EXAFS oscillations are determined by the local structure around the absorbing atomic species. Indium atoms at the planar In(1) site are surrounded by 4 Ce and 8 In near neighbors, at distances 3.268 Å and 3.286 Å, respectively [22]. On the other hand, Indium atoms at the low symmetry In(2) site have 2 Co and 1 In immediate neighbors at 2.723 Å and 2.879 Å, respectively, followed by 4 In’s at 3.268 Å, and 2 In and 2 Ce neighbors at a distance 3.286 Å. To help us compare the difference between the two sites, we have generated a theoretical EXAFS function $\chi(k)$ for each site. The Fourier transform (FT) of the simulated EXAFS function for both sites is presented in Fig. 3. Note that in the low $R$ region for the In(2) site, there is a well resolved peak at ~ 2.4 Å (labelled A), which is mainly due to the 2 Co and 1 In near neighbors (due to the phase shift of the photoelectron at the absorbing and backscattering atoms, the peak positions are shifted by small known amounts from the actual pair distances). In addition, the peak at ~3.0 Å (labelled B), which is due to Ce and In neighbors, is larger for the In(1) site since it has more neighbors contributing to that peak, namely 4 Ce’s and 8 In’s, compared to the In(2) site, which has 2 Ce and 6 In neighbors at this distance. The lower panel in Fig. 3 compares the FT for In K-edge CeCoIn$_5$ data with Sn K-edge CeCoIn$_{4.76}$Sn$_{0.24}$ data. The A peak is clearly larger and the B peak smaller.

![FIG. 1: Superconducting transition temperature from specific heat data [21] as a function of $x$ in CeCoIn$_{5-x}$Sn$_x$. The inset shows the crystal structure of CeCoIn$_5$.](image)

![FIG. 2: $k\chi(k)$ data for CeCoIn$_{4.76}$Sn$_{0.24}$ at 30 K.](image)
in the parent compound than in the Sn-substituted one. These data therefore qualitatively indicate that fewer Sn atoms reside on the In(2) sites than expected from a random distribution over all available In sites.

The fraction of Sn atoms going to the In(1) site has been estimated by fitting the EXAFS signal to a linear combination of standards generated for the two sites (Fig. 4). The overall amplitude reduction factor $S_0^2$, the coordination distances $R$, and the pair distribution widths ($\sigma$’s) were also allowed to vary. Only single scattering paths were included. Consistent with the observed FT features, the fit results show a major fraction of Sn predominantly occupying the In(1) site. Despite the fact that there are four times as many In(2) sites as In(1) sites, the fraction of Sn atoms going to the In(1) site is 0.6(1), 0.6(1), 0.5(1), and 0.6(1) for $x=0.09$, 0.12, 0.18, and 0.24, respectively. With the exception of the Sn(2)-Co pair distance, which shows a 0.05-0.09 Å contraction, all other pair distances for the In(1) and In(2) sites agree with previously reported values for CeCoIn$_5$ [22, 27].

Our findings are particularly significant when one considers the observed bulk physical properties of Sn-substituted CeCoIn$_5$ samples. In particular, these results help explain the much larger effect of Sn substitution as opposed to Rh or Ir substitution on $T_c$. In a three-dimensional superconductor, Abrikosov-Gorkov (AG) impurity scattering [29] would be similar for, say, Rh and Sn substitutions. However, our local structure studies show that Sn preferentially substitutes onto the Ce-In planes, which should enhance the impurity scattering in a 2D superconductor. One effect of this Sn distribution is to decrease the mean distance between Sn(1) impurities as compared to the superconducting coherence length $\xi_a$, which has been estimated to be $\approx 81$ Å in CeCoIn$_5$ [14, 30], or about 17-18 unit cells. If Sn were randomly distributed on the two In sites, the nearest distance between Sn(1) atoms would be about 120 Å, which should have only a small impact on $T_c$. Instead, our results indicate that the distance between Sn(1) atoms is about 50 Å, or about 11-12 unit cells. This impurity separation is within the estimate of $\xi_a$, and hence should have a large effect on $T_c$.

The Sn-substitution situation is much more similar to substituting La for Ce. However, despite modifying the Ce-In plane, La has a less dramatic effect on SC as compared to Sn substitution [20]. This fact strongly suggests that Sn substitution has a stronger effect than La substitution by inducing additional scattering mechanisms in the Ce-In planes. Since AG-impurity scattering is enhanced by scattering off Kondo singlets [31], it is easy to imagine that Sn impurities strongly increase $T_K$ as occurs in CeIn$_{3-x}$Sn$_x$ [32, 33], as opposed to removing the Kondo singlet by La substitution. In fact, the temperature at which the electrical resistivity is a maximum is observed to increase with Sn concentration, indicating a probable increase in $T_K$ [21]. However, it is not clear $a$ priori whether Sn substitution should increase or decrease $T_K$. $T_K$ is commonly given by $k_BT_K \approx E_F \exp(-\epsilon_f/V^2\theta)$, where $k_B$ is Boltzmann’s constant, $V$ is the local-moment/conduction-electron hybridization matrix element, $\epsilon_f$ is the $f$-level energy below
the Fermi-level, and $q$ is the electronic density of states at the Fermi-level $E_F$. Therefore an increasing $T_K$ implies either an increasing $E_F$, $q$, or $V$, or a decreasing $\epsilon_f$. It is difficult to predict the effect of Sn substitution on $E_F$ and $\epsilon_f$. In the tight binding formalism the hybridization strength between the Ce $f$ and the In (or Sn) $p$-electrons is of order $V_{fp} \sim (r_p^2 r_f^2)^{1/2}/d^2$, where $r_p$ and $r_f$ are tabulated electron wave function radii for a particular atom and $d$ is the distance between the atoms [34]. Sn has a smaller $r_p$ value than In [35], so $V_{fp}$ should be weaker in the Sn-substituted material, and hence should decrease $T_K$ [34]. On the other hand, Sn has one more $p$-electron than In, so an increased conduction density of states in the Sn-substituted material may be responsible for the observed increase in $T_K$, similarly as suggested for CeIn$_{3-\delta}$Sn$_{\delta}$ [32].

It is important to emphasize that given the distances between Sn impurity centers, the perturbations they induce in $T_K$ will have some local character. These local perturbations will thus generate a distribution of $T_K$’s (similar to a Kondo disorder model [36]). Finally, assuming the SC pairing mechanism is magnetically mediated through antiferromagnetic fluctuations, such local changes in the coupling parameters could cause pair breaking by directly perturbing the pairing mechanism.

To summarize, the local structure around Sn in CeCoIn$_{5-\delta}$Sn$_{\delta}$ ($x = 0.09, 0.12, 0.18,$ and $0.24$) has been probed by EXAFS. Our fit results show that the majority of Sn atoms preferentially reside on the planar In(1) sites. Impurity scattering is therefore primarily confined to the Ce-In planes, in contrast to substituting with Rh or Ir, which substitute outside of this plane. This result implies that the impurity separation is much shorter than one would obtain by a random distribution of Sn atoms on In sites, and in fact one obtains a separation distance within the estimate of the superconducting coherence length $\xi_a$ in CeCoIn$_5$ [14, 30]. Our results further show that compared to La substitution onto the Ce sites, Sn substitution increases the planar scattering more effectively and this might be due to an increase in the Kondo singlet scattering. Taken together, these results indicate that the rapid suppression of $T_c$ in CeCoIn$_{5-\delta}$Sn$_{\delta}$ is due to an enhanced perturbation of a superconducting state that is confined within the Ce-In planes, consistent with the 2D-like electronic structure of CeCoIn$_5$.

We acknowledge Dr. J. D. Denlinger for useful conversations. Work at Lawrence Berkeley National Laboratory was supported by the Director, Office of Science, Office of Basic Energy Sciences (OBES), of the U.S. Department of Energy (DOE) under contract No. AC03-76SF00098. Work at the University of Nevada was supported by DOE/EPSCoR contract No. DE-FG02-00ER45835 and DOE Cooperative Agreement DE-FC08-98NV13410. P. G. P. thanks Fapesp-SP and CNPq-Br. XAS data were collected at SSRL, a national user facility operated by Stanford University on the behalf of DOE/OBES.

[27] See EPAPS Document No. E-PRLETAO-AB-CDEFGH for detailed structural fit results for the In(1) and In(2) sites. A direct link to this document may be found in the online article’s HTML reference section. The document may also be reached via the EPAPS homepage (http://www.aip.org/publishervs/epaps.html) or from ftp.aip.org in the directory /epaps/. See EPAPS homepage for more information.